

HiPerFRED²

$$V_{RRM} = 200V$$

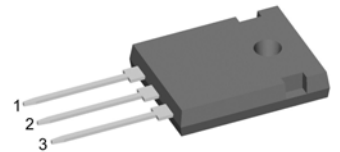
$$I_{FAV} = 2 \times 30A$$

$$t_{rr} = 35ns$$

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DPG60C200HB



Backside: cathode

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Fast Diode				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			200	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			200	V
I_R	reverse current, drain current	$V_R = 200 V$	$T_{VJ} = 25^{\circ}C$		1	μA
		$V_R = 200 V$	$T_{VJ} = 150^{\circ}C$		0.1	mA
V_F	forward voltage drop	$I_F = 30 A$	$T_{VJ} = 25^{\circ}C$		1.34	V
					1.63	V
		$I_F = 60 A$	$T_{VJ} = 150^{\circ}C$		1.06	V
					1.39	V
I_{FAV}	average forward current	$T_C = 140^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}C$		30	A
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}C$		0.70	V
r_F	slope resistance				10.5	m Ω
R_{thJC}	thermal resistance junction to case				0.95	K/W
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		160	W
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		360	A
C_J	junction capacitance	$V_R = 150 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		42	pF
I_{RM}	max. reverse recovery current	} $I_F = 30 A; V_R = 130 V$ $-di_F/dt = 200 A/\mu s$	$T_{VJ} = 25^{\circ}C$		3	A
t_{rr}	reverse recovery time		$T_{VJ} = 125^{\circ}C$		7	A
			$T_{VJ} = 25^{\circ}C$		35	ns
			$T_{VJ} = 125^{\circ}C$		55	ns

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			50	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Part number

- D = Diode
- P = HiPerFRED
- G = extreme fast
- 60 = Current Rating [A]
- C = Common Cathode
- 200 = Reverse Voltage [V]
- HB = TO-247AD (3)

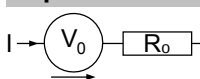
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG60C200HB	DPG60C200HB	Tube	30	506294

Similar Part	Package	Voltage class
DPG60C200QB	TO-3P (3)	200
DPF60C200HB	TO-247AD (3)	200
DPF60C200HJ	ISOPLUS247 (3)	200

Equivalent Circuits for Simulation

* on die level

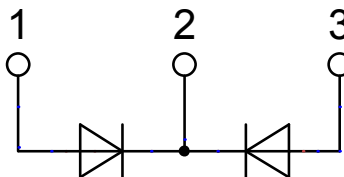
$T_{VJ} = 175^\circ\text{C}$



Fast Diode

$V_{0\ max}$	threshold voltage	0.7	V
$R_{0\ max}$	slope resistance *	7.9	mΩ

Outlines TO-247



Fast Diode

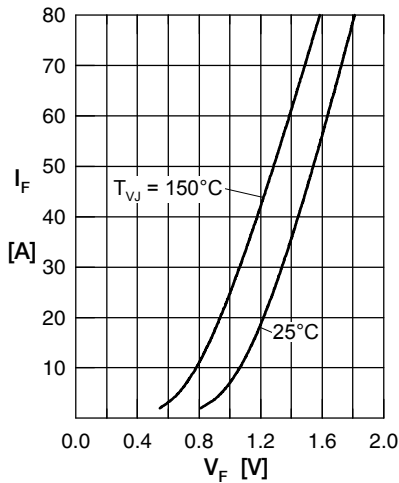


Fig. 1 Forward current I_F versus V_F

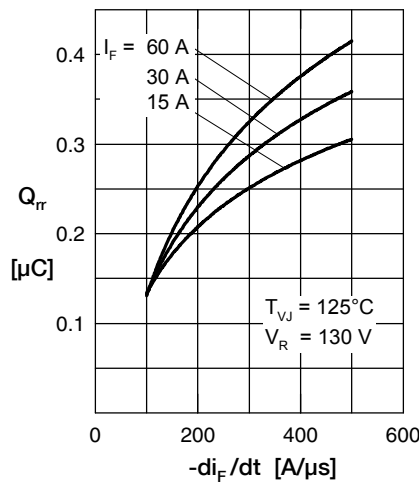


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

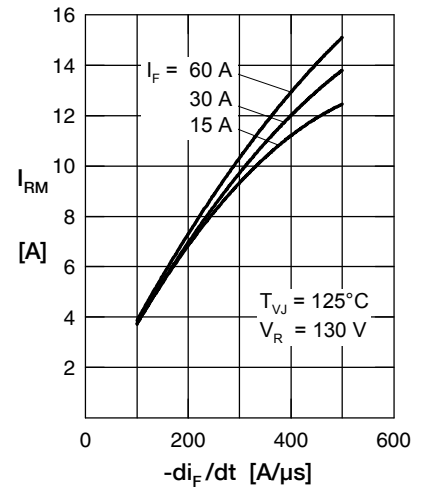


Fig. 3 Typ. reverse recov. current I_{RM} versus $-di_F/dt$

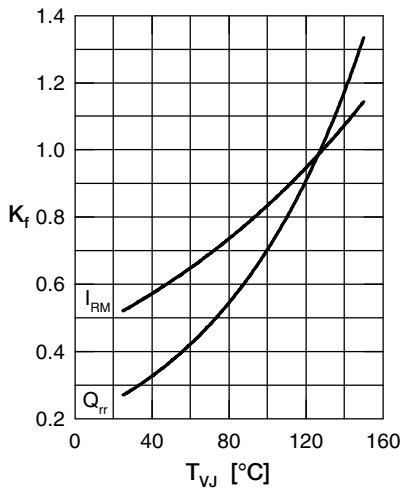


Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

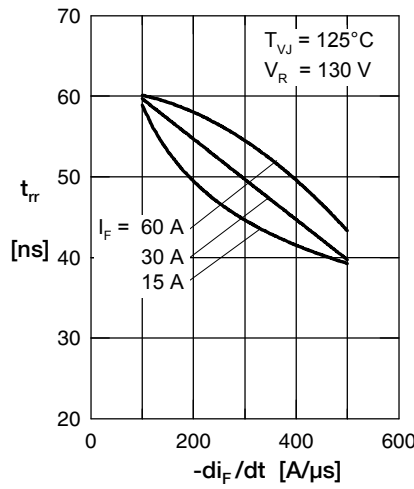


Fig. 5 Typ. reverse recov. time t_{rr} versus $-di_F/dt$

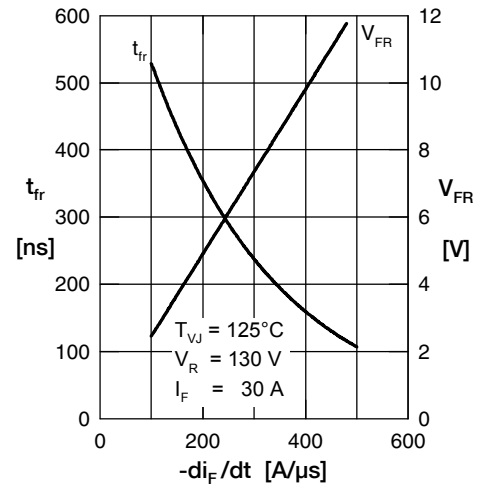


Fig. 6 Typ. forward recov. voltage V_{FR} and t_{fr} versus di_F/dt

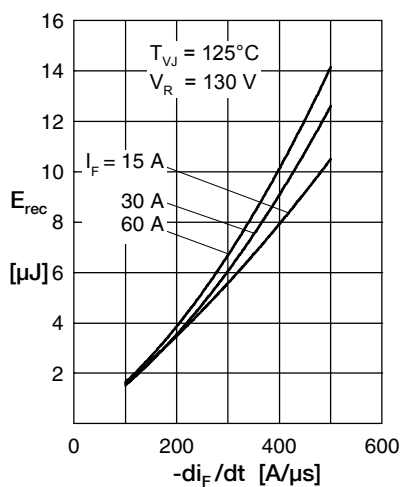


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

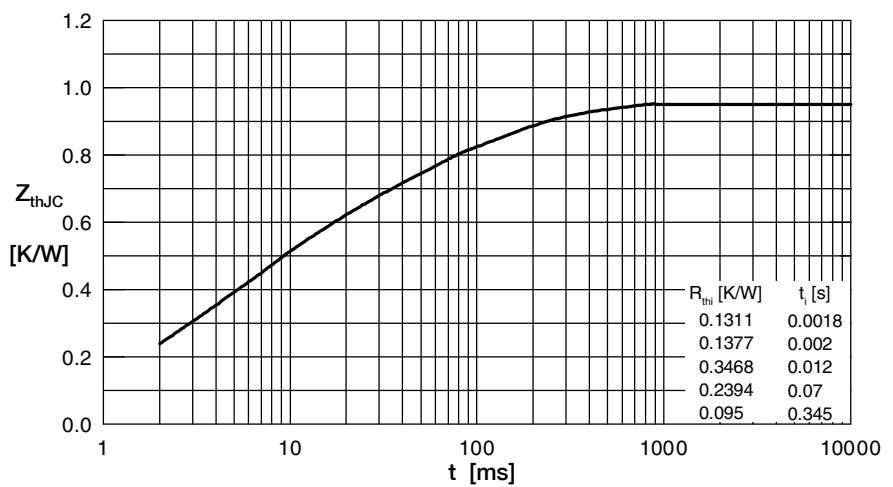


Fig. 8 Transient thermal impedance junction to case